

/ Descriptions

WR0585 M M E SQS æ M y s ll 1 Silicon PNP transistor in a TO-252 Plastic Package.

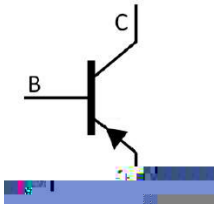
/ Features

Low $V_{CE(sat)}$, complements the 2SD1760.

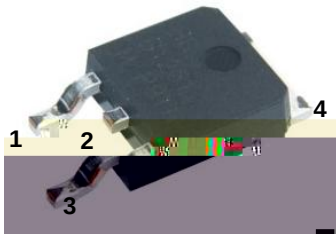
/ Applications

Power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2,4 χ Collector PIN 3 χ Emitter

/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	P	Q	R
h _{FE} Range	82 180	120 270	180 390

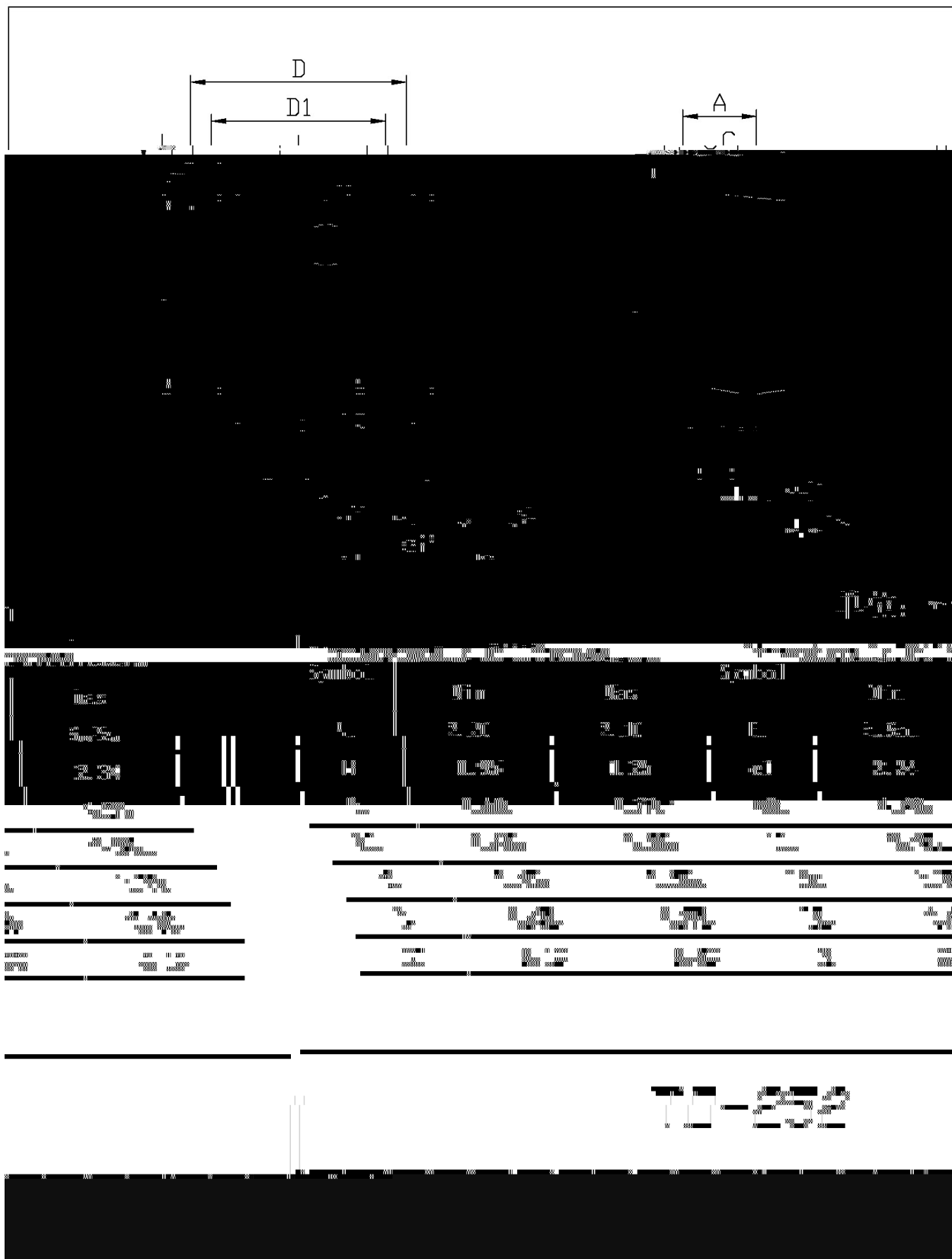
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	$P_C(T_c=25)$	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

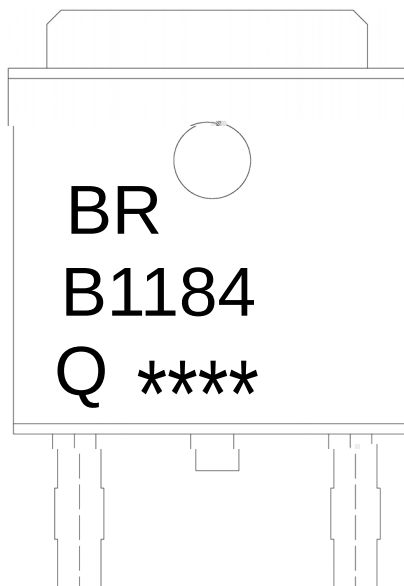
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-50\text{ A}$ $I_E=0$	-60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0\text{mA}$ $I_B=0$	-50			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-50\text{ A}$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-40\text{V}$ $I_E=0$			-1.0	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-4.0\text{V}$ $I_C=0$			-1.0	A
DC Current Gain	h_{FE}	$V_{CE}=-3.0\text{V}$ $I_C=-0.5\text{A}$	82		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2.0\text{A}$ $I_B=-0.2\text{A}$			-1.0	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-1.5\text{A}$ $I_B=-0.15\text{A}$			-1.2	V
Transition Frequency	f_T	$V_{CE}=-5.0\text{V}$ $I_C=-0.5\text{A}$ $f=30\text{MHz}$		70		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}$ $I_E=0$ $f=1.0\text{MHz}$		50		pF

/ Package Dimensions



/ Marking Instructions



Б " X

BR X

E44; 7 X

T=

---- X

Note:

BR:

B1184:

Q:

****:

Б 3 " П

Б 3 " П

Б h_{FE} ' 6 П

Б 1 f 7 " П 1 8 1 f 7 " П

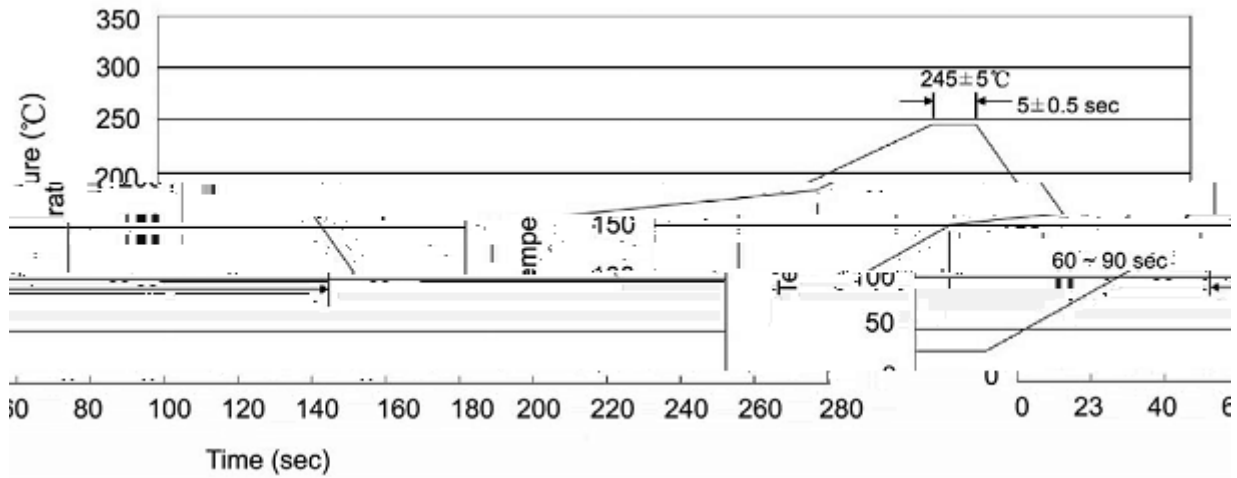
Company Code

Product Type.

h_{FE} Classifications Symbol

Lot No. Code, code change with Lot No.

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



注意：

1. 预加热：25~150℃，时间：60~90sec；
2. 峰值温度：245±5℃，持续时间：5±0.5sec；
3. 冷却速度：2~10℃/sec。

Note:

1. Preheating: 25~150℃, Time: 60~90sec.
2. Peak Temp.: 245±5℃, Duration: 5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

锡焊温度：260±5℃ 时间：10±1 sec. Temp.: 260±5 Time: 10±1 sec

/ Packaging SPEC.

卷带 / REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	5	25,000	13 × 16	360×360×50	385×257×392

管装 / TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

/ Notices